TOSHIBA Field Effect Transistor Silicon P Channel MOS Type (L^2 - π -MOSV)

2SJ360

Chopper Regulator, DC-DC Converter and Motor Drive Applications

• 4-V gate drive

• Low drain–source ON resistance : RDS (ON) = 0.55 Ω (typ.)

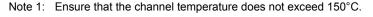
• High forward transfer admittance $: |Y_{fs}| = 0.9 \text{ S (typ.)}$

• Low leakage current $: I_{DSS} = -100 \,\mu\text{A} \,(\text{max}) \,(V_{DS} = -60 \,\text{V})$

• Enhancement mode : $V_{th} = -0.8 \sim -2.0 \text{ V (V}_{DS} = -10 \text{ V, I}_{D} = -1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteri	stics	Symbol	Rating	Unit	
Drain-source voltage		V_{DSS}	-60	V	
Drain-gate voltage (R _{GS} = 20 kΩ)		V_{DGR}	-60	٧	
Gate-source voltage		V_{GSS}	±20	٧	
Drain current	DC (Note 1)	I_{D}	-1	Α	
	Pulse (Note 1)	I_{DP}	-3	Α	
Drain power dissipatio	n	P_{D}	0.5	W	
Drain power dissipation (Note 2)		P_{D}	1.5	W	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	



- Note 2: Mounted on a ceramic substrate (25.4 mm × 25.4 mm × 0.8 mm)
- Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

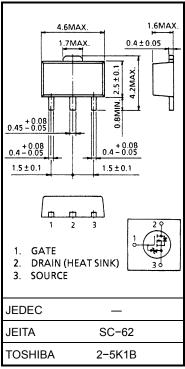
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to ambient	R _{th (ch-a)}	250	°C / W

This transistor is an electrostatic-sensitive device.

Please handle with caution.

Unit: mm



Weight: 0.05 g (typ.)



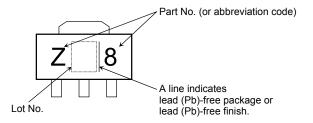
Electrical Characteristics (Ta = 25°C)

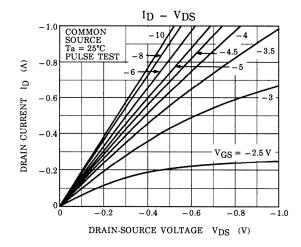
Charac	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage cu	ırrent	I _{GSS}	V _{GS} = ±16 V, V _{DS} = 0 V	_	_	±10	μΑ
Drain cut-off cu	rrent	I _{DSS}	V _{DS} = -60 V, V _{GS} = 0 V	_	_	-100	μΑ
Drain-source br	eakdown voltage	V (BR) DSS	I _D = -10 mA, V _{GS} = 0 V	-60	_	_	V
Gate threshold v	oltage/	V_{th}	V _{DS} = -10 V, I _D = -1 mA	-0.8	_	-2.0	V
Drain-source ON resistance		R _{DS (ON)}	V _{GS} = -4 V, I _D = -0.5 A	_	0.86	1.2	Ω
			$V_{GS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	_	0.55	0.73	32
Forward transfe	r admittance	Y _{fs}	$V_{DS} = -10 \text{ V}, I_D = -0.5 \text{ A}$	0.5	0.9	_	S
Input capacitano	e	C _{iss}			155	1	pF
Reverse transfe	r capacitance	C _{rss}	V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz	_	20	_	
Output capacitance		Coss		_	75	_	
Switching time	Rise time	t _r	$V_{GS} \xrightarrow{0V} I_{D} = -0.5A$ V_{OUT} $R_{L} = 60\Omega$ $V_{DD} = -30V$	_	17	_	
	Turn-on time	t _{on}		_	20	_	nc
	Fall time	t _f		l	20	l	ns
	Turn-off time	t _{off}	Duty $\leq 1\%$, $t_{W} = 10 \mu s$	-	100	-	
Total gate charge (Gate-source plus gate-drain)		Qg	V _{DD} ≈ -48 V, V _{GS} = -10 V, I _D = -1 A		6.5		
Gate-source charge		Q _{gs}		_	4.5	_	nC
Gate-drain ("miller") charge		Q _{gd}		_	2.0		

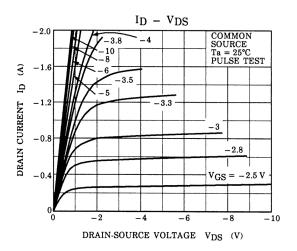
Source-Drain Ratings and Characteristics (Ta = 25°C)

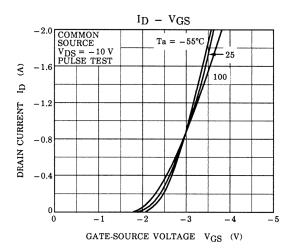
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current (Note 1)	I _{DR}	_	_	_	-1	Α
Pulse drain reverse current (Note 1)	I _{DRP}	_	_	_	-3	Α
Forward voltage (diode)	V _{DSF}	I _{DR} = -1 A, V _{GS} = 0 V	_	_	1.7	V
Reverse recovery time	t _{rr}	I _{DR} = -1 A, V _{GS} = 0 V dI _{DR} / dt = 50 A / μs	_	50	_	ns
Reverse recovery charge	Q _{rr}		_	50	_	μC

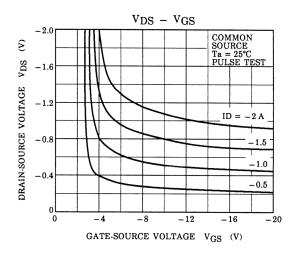
Marking

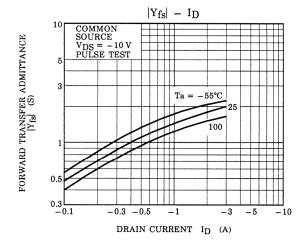


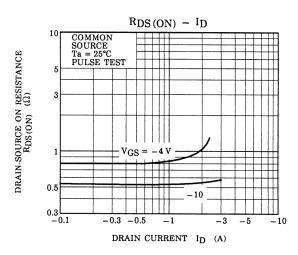




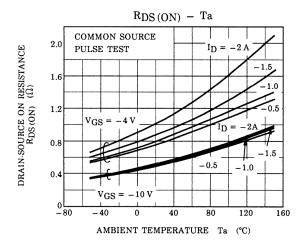


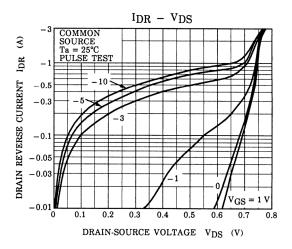


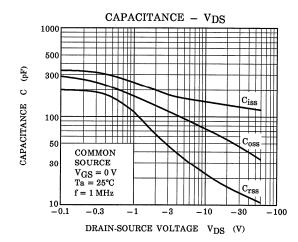


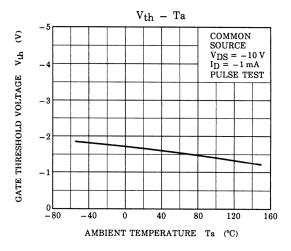


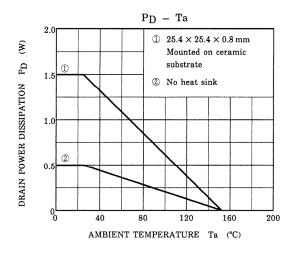
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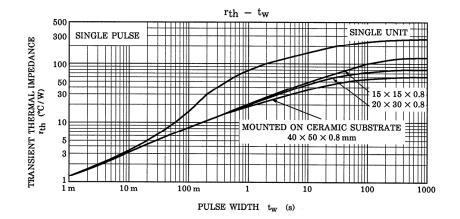


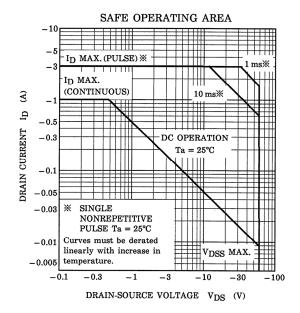






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